

RFMD®

RFGA2012

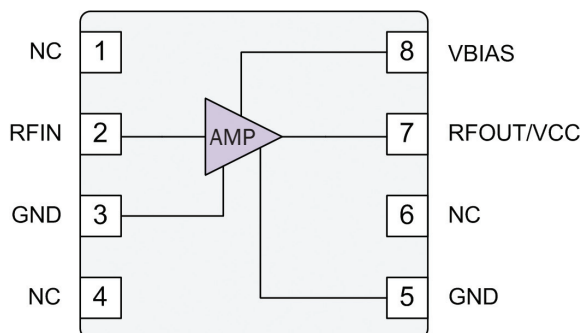
InGaP HBT Low Power Linear Amplifier, 50 to 3000MHz



Specifically designed to achieve high OIP3 with minimal DC power, RFGA2012 has proven ultra-linear performance in standard frequency bands from 150MHz to 3GHz. The RFGA2012 features a VBIAS pin that allows users to optimize the quiescent current for specific requirements. The VBIAS pin also serves as a power-down pin. Offering 1000V HBM ESD ruggedness, the device is manufactured using RFMD's InGaP HBT process to minimize Beta process variation.

SPECIFICATIONS

Frequency (MHz)	P1dB (dBm)	OIP3 (dBm)	Gain (dB)	Noise Figure (dB)	Vcc (V)	Package	Part Number
150	12.5	30.0	25.0	3.8	3.3	DFN	RFGA2012
900	14.5	34.5	19.0	2.7	3.3	DFN	RFGA2012
1960	13.5	35.0	14.5	1.6	3.3	DFN	RFGA2012
2650	15.0	34.0	12.0	1.6	3.3	DFN	RFGA2012



FEATURES

- High OIP3 = 35dBm at 1960MHz
- Low DC power = 3.3V, 23mA
- Low noise figure = 1.6dB at 1960MHz
- 50 to 3000MHz operation
- Power-down capability
- Class 1C (1000V) HBM ESD rating
- MSL 1 rating
- Common platform compatible
- Applications include: low-power linear gain stage; IF, cellular, DCS, PCS, UMTS, WiFi, WiMAX, TD-SCDMA, LTE amplifiers, low-power low noise amplifiers

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7628 Thorndike Rd., Greensboro, NC 27409-9421 USA • Phone 336.664.1233



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